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First Named Inventor	Wang Zhongze	<b>INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</b>
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Title: FET HAVING EPITAXIAL SILICON GROWTH		Sheet 1 of 1

U.S. Patent References				
Examiner Initials	Document No.	Publication Date (mm/dd/yy)	Name	Filing Date (mm/dd/yy)
WP	09/713,844	Unknown	Abbott ete al.	11/15/00
	5,908,313	06/01/99	Chau et al.	12/31/96
	6,156,589	12/05/00	Noble	09/03/98
	6,180,494 B1	01/30/01	Manning	03/11/99
	6,274,913 B1	08/14/01	Brigham et al.	10/05/98
	6,300,219 B1	10/09/01	Doan et al.	08/30/99
	6,358,798 B1	03/19/02	Chen	09/06/00
	6,388,294 B1	05/14/02	Radens et al.	11/22/00
	6,391,726 B1	05/21/02	Manning	06/29/00

Foreign Patent References					
Examiner Initials	Foreign Patent		Name	Publication Date	Translation
	Country	No.			

Other References	
Examiner Initials	Author, Title, Date, Pages, etc.
WP	S. Wolf et al, "Silicon Epitaxial Film Growth," <u>Silicon Processing for the VLSI Era</u> , Vol. 1, 1986, pp. 124-160.

Examiner Signature	<i>Michael Hanh</i>	Date Considered	12/15/2005
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

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